

**Inchange Semiconductor**

**Product Specification**

**Silicon PNP Power Transistors**

**2SB1096**

**DESCRIPTION**

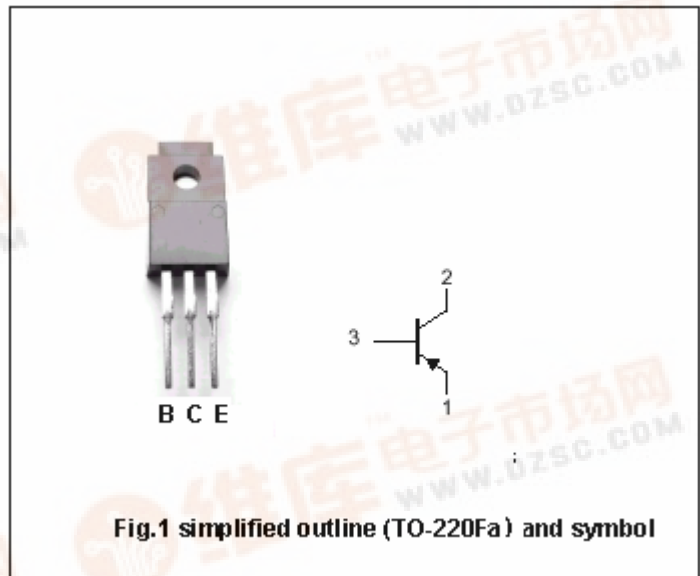
- With TO-220Fa package
- High breakdown voltage
- Complement to type 2SD1587

**APPLICATIONS**

- For TV vertical output applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-200	V
V <sub>CEO</sub>	Collector -emitter voltage	Open base	-150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-2	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25	2.0	W
		T <sub>C</sub> =25	25	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

## Silicon PNP Power Transistors

## 2SB1096

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-30mA; I <sub>B</sub> =0	-150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-500mA ; I <sub>B</sub> =-50mA			-1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-500mA ; I <sub>B</sub> =-50mA			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-150V; I <sub>E</sub> =0			-50	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-50	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.4A ; V <sub>CE</sub> =-10V	40		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.4A; V <sub>CE</sub> =-10V		5		MHz

◆ h<sub>FE</sub> Classifications

M	L	K
40-80	60-120	100-200

PACKAGE OUTLINE

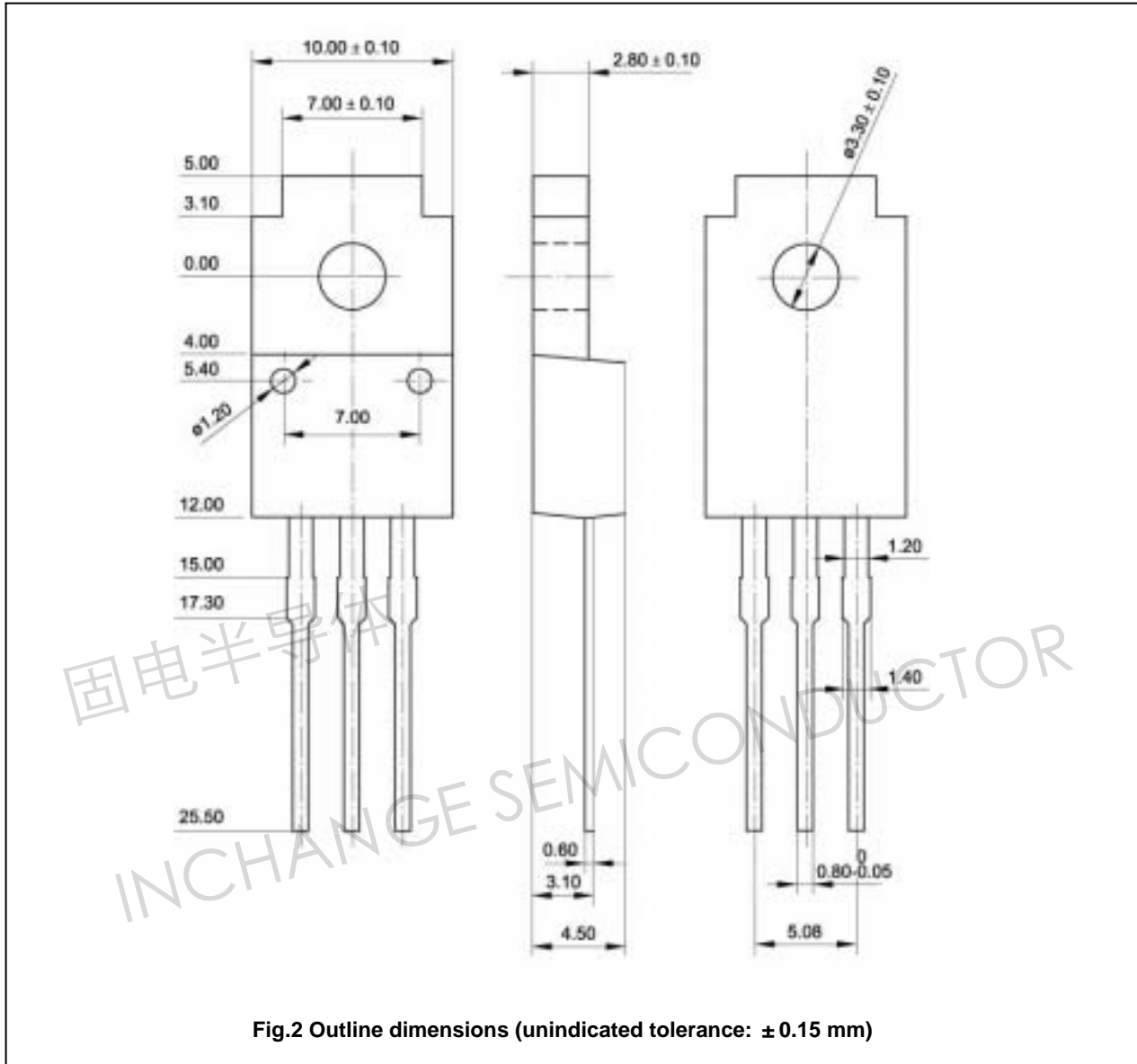


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)